

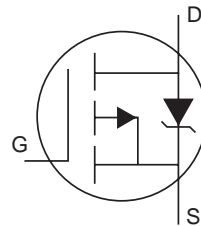
TO-220AB

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- P-Channel
- Fully Avalanche Rated


**Power MOSFET**

## Description

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



$$V_{DSS} = -100V$$

$$R_{DS(on)} = 0.06\Omega$$

$$I_D = -40A$$

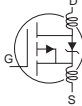
## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-40	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-29	
$I_{DM}$	Pulsed Drain Current ①	-140	
$P_D @ T_C = 25^\circ C$	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy②	780	mJ
$I_{AR}$	Avalanche Current③	-21	A
$E_{AR}$	Repetitive Avalanche Energy①	20	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

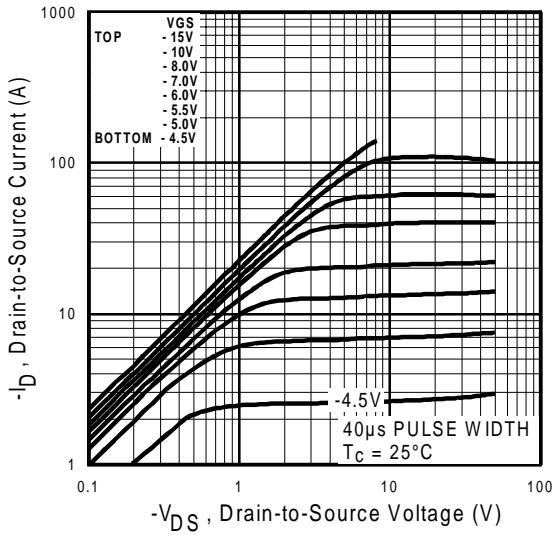
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-100	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.11	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.06	$\Omega$	$V_{GS} = -10V, I_D = -24A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
$g_{fs}$	Forward Transconductance	10	—	—	S	$V_{DS} = -50V, I_D = -21A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-25	$\mu A$	$V_{DS} = -100V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = -80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
$Q_g$	Total Gate Charge	—	—	180	nC	$I_D = -21A$
$Q_{gs}$	Gate-to-Source Charge	—	—	25		$V_{DS} = -80V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	97		$V_{GS} = -10V$ , See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	17	—	ns	$V_{DD} = -50V$
$t_r$	Rise Time	—	86	—		$I_D = -21A$
$t_{d(off)}$	Turn-Off Delay Time	—	79	—		$R_G = 2.5\Omega$
$t_f$	Fall Time	—	81	—		$R_D = 2.4\Omega$ , See Fig. 10 ④
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	2700	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	790	—		$V_{DS} = -25V$
$C_{rss}$	Reverse Transfer Capacitance	—	450	—		$f = 1.0\text{MHz}$ , See Fig. 5

## Source-Drain Ratings and Characteristics

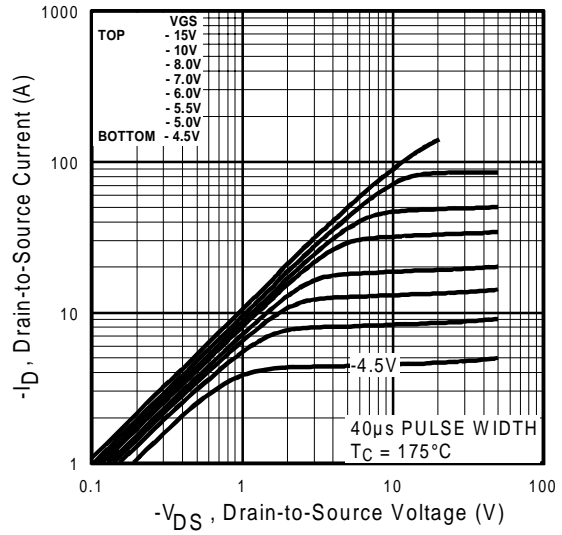
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-40	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-140		
$V_{SD}$	Diode Forward Voltage	—	—	-1.6	V	$T_J = 25^\circ\text{C}, I_S = -21A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	170	260	ns	$T_J = 25^\circ\text{C}, I_F = -21A$
$Q_{rr}$	Reverse Recovery Charge	—	1.2	1.8	$\mu C$	$di/dt = -100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

### Notes:

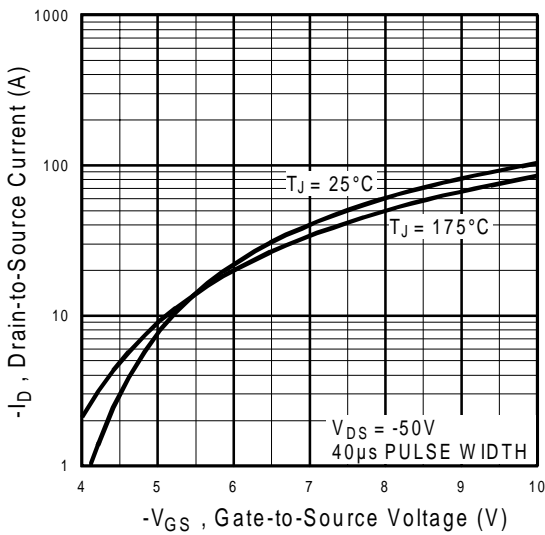
- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ②  $V_{DD} = -25V$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 3.5\text{mH}$   
 $R_G = 25\Omega, I_{AS} = -21A$ . (See Figure 12)
- ③  $I_{SD} \leq -21A, di/dt \leq -480A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .



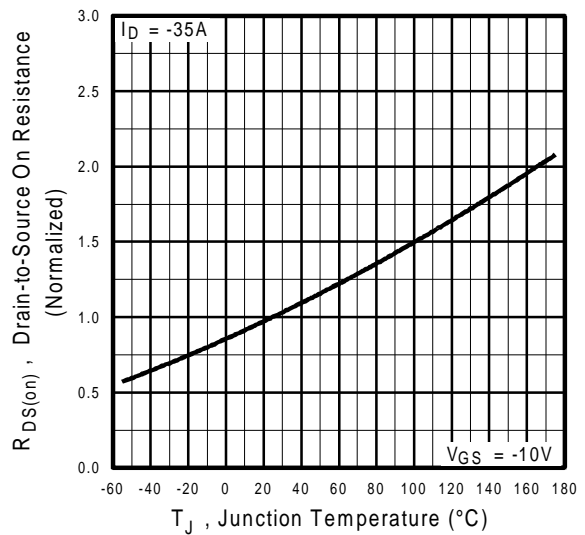
**Fig 1.** Typical Output Characteristics



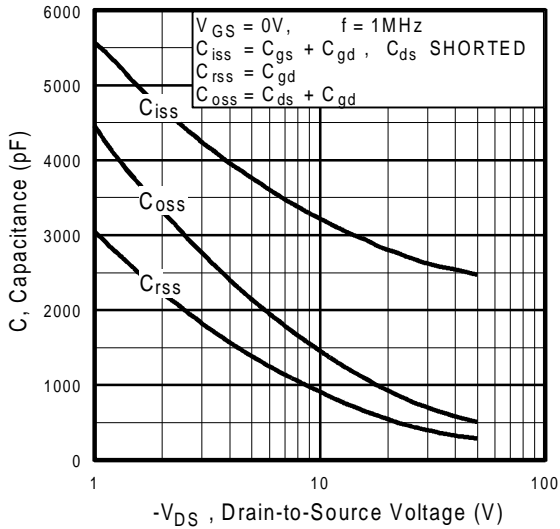
**Fig 2.** Typical Output Characteristics



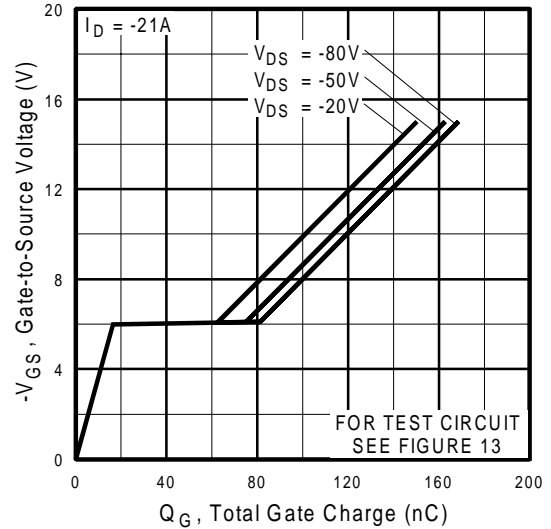
**Fig 3.** Typical Transfer Characteristics



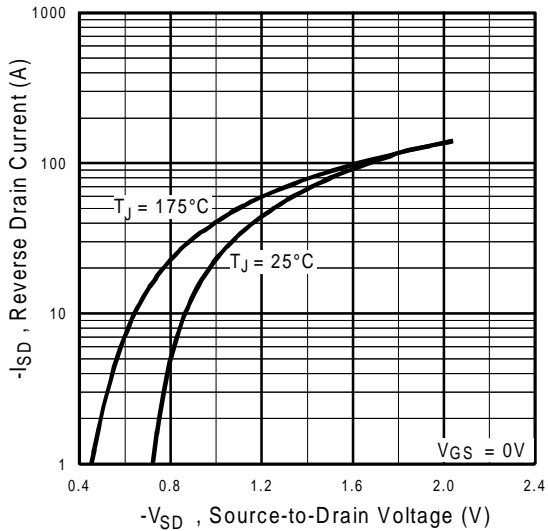
**Fig 4.** Normalized On-Resistance Vs. Temperature



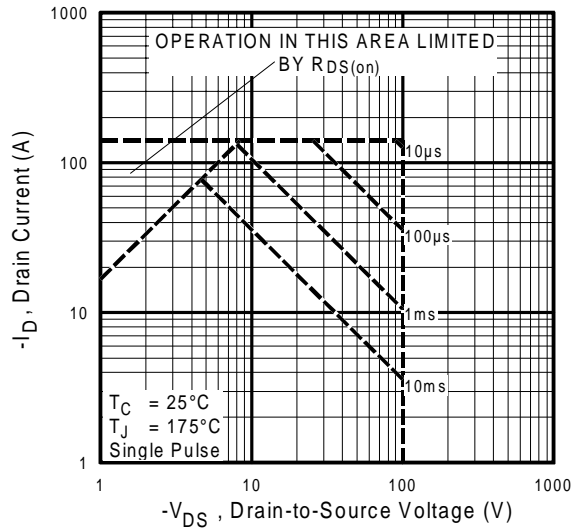
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



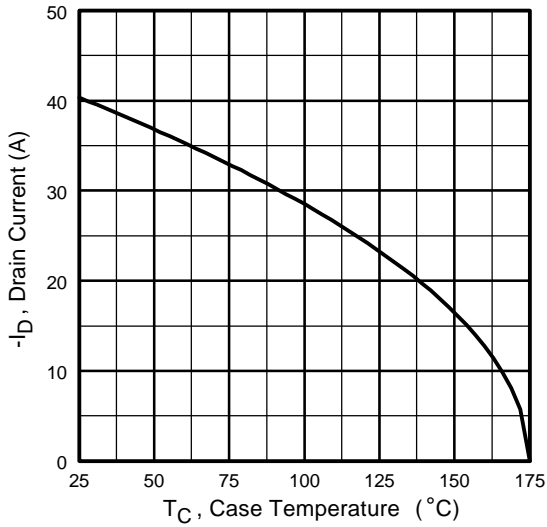
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



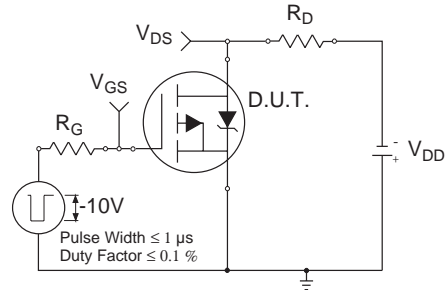
**Fig 7.** Typical Source-Drain Diode Forward Voltage



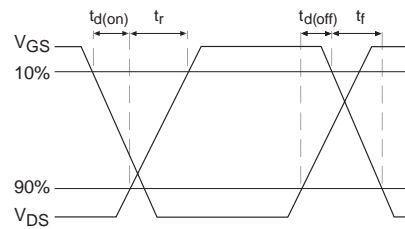
**Fig 8.** Maximum Safe Operating Area



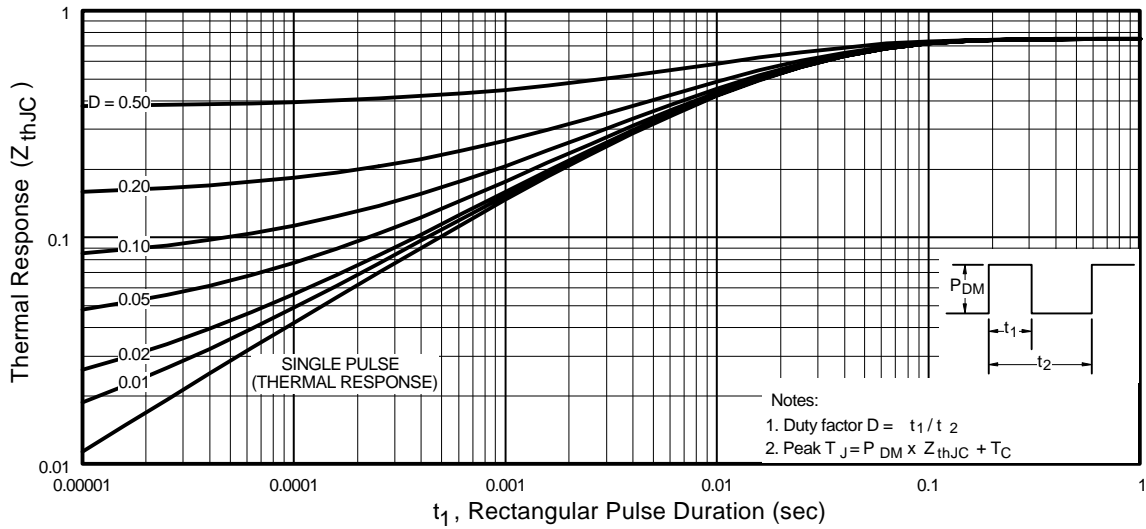
**Fig 9.** Maximum Drain Current Vs. Case Temperature



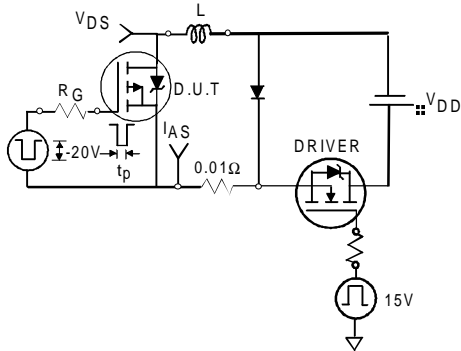
**Fig 10a.** Switching Time Test Circuit



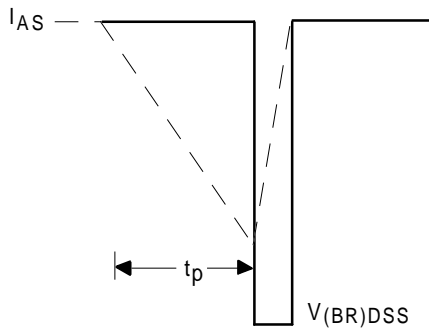
**Fig 10b.** Switching Time Waveforms



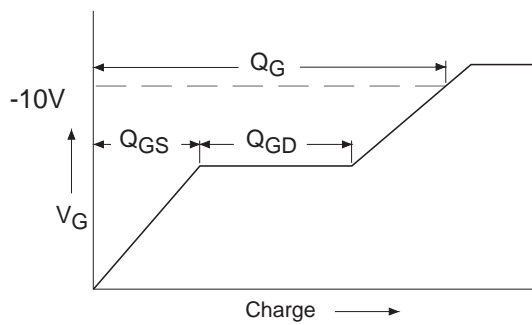
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



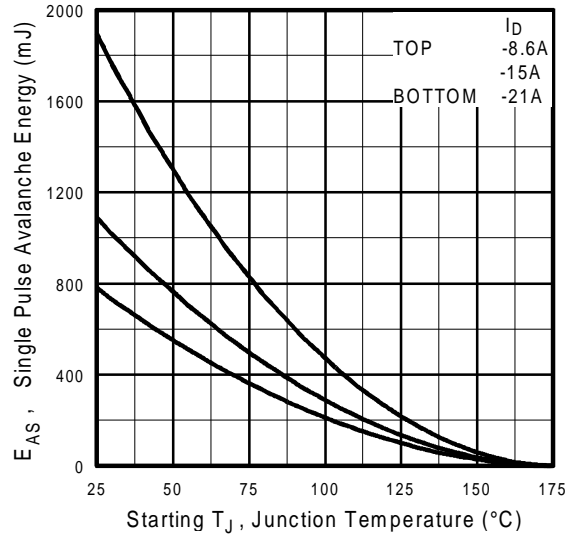
**Fig 12a.** Unclamped Inductive Test Circuit



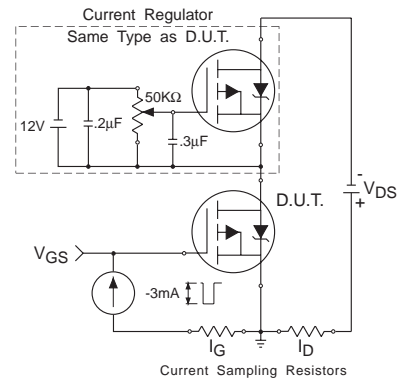
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform

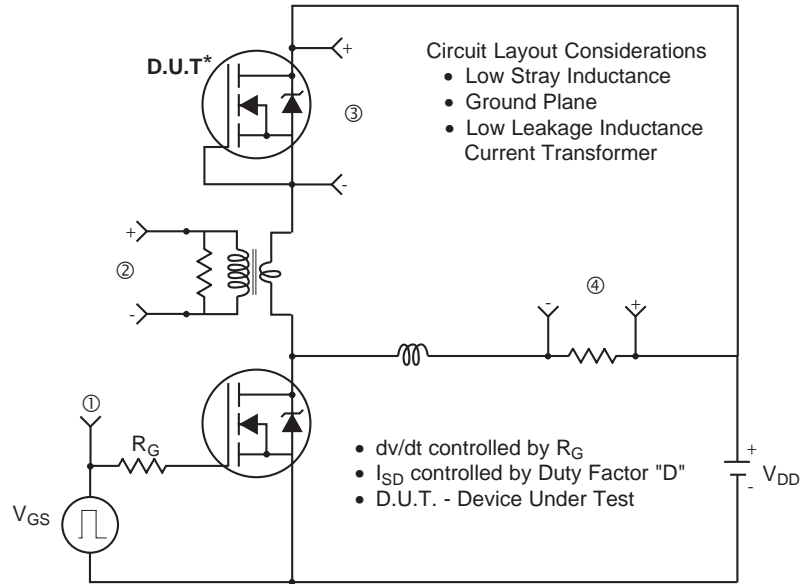


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

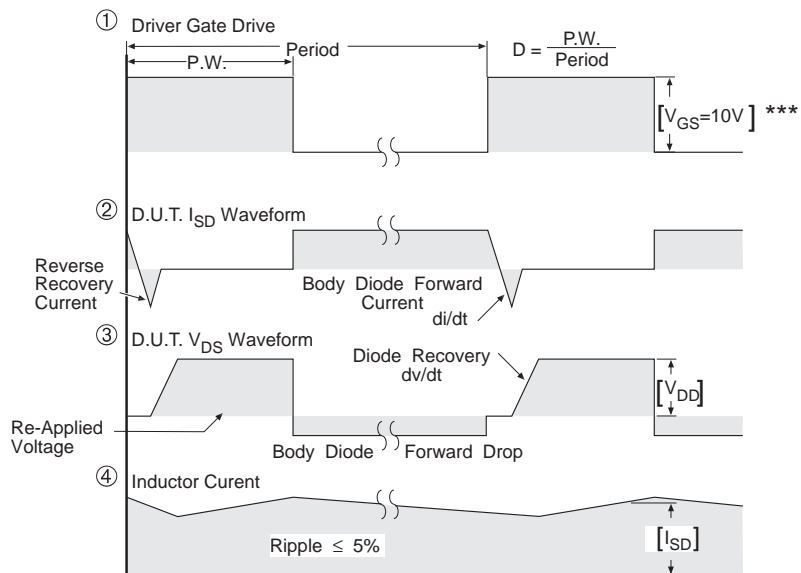


**Fig 13b.** Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity of D.U.T for P-Channel



\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

**Fig 14. For P-Channel HEXFETS**

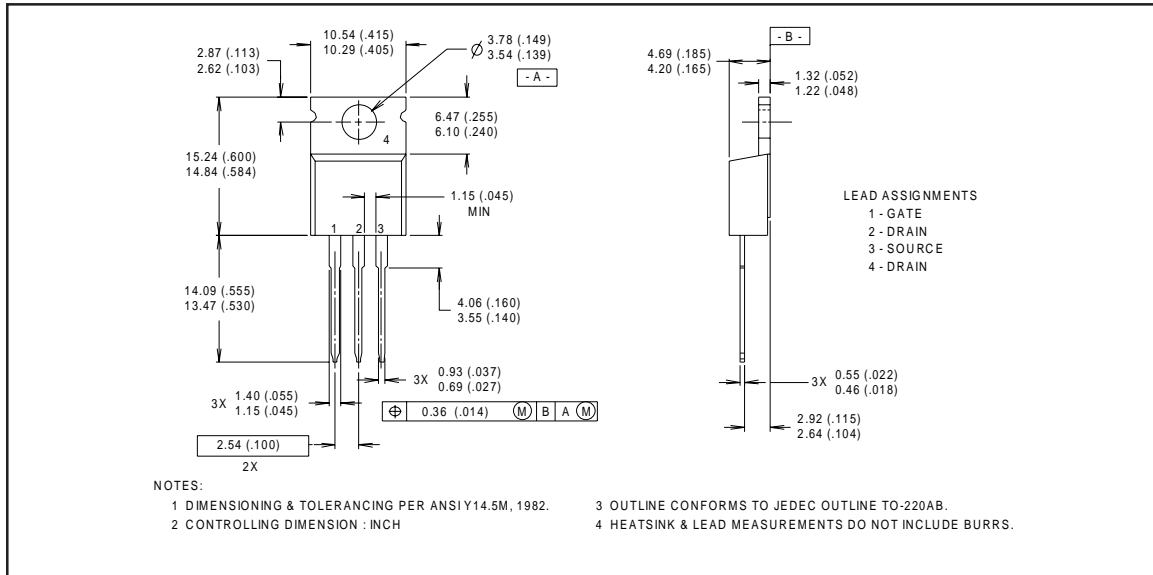


# IRF5210

## Package Outline

### TO-220AB Outline

Dimensions are shown in millimeters (inches)



## Part Marking Information

### TO-220AB

EXAMPLE : THIS IS AN IRF1010  
WITH ASSEMBLY  
LOT CODE 9B1M

